

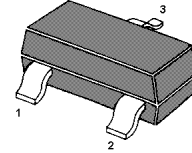
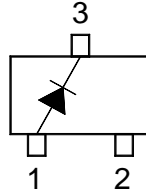
# SB491D

## SILICON EPITAXIAL PLANAR SCHOTTKY BARRIER DIODE

for low power rectification and switching power supply  
power supply applications

### Feature

- Ultra Low  $V_F$



SOT-23 Plastic Package

### Marking

Marking Code: FJ

### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Peak Reverse Voltage	$V_{RM}$	25	V
DC Reverse Voltage	$V_R$	20	V
DC Forward Current	$I_F$	1	A
Peak Forward Surge Current <sup>1)</sup>	$I_{FSM}$	3	A
Junction Temperature	$T_j$	125	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	-40 to +125	$^\circ\text{C}$

<sup>1)</sup> 60Hz for 1  $\mu\text{s}$

### Characteristics at $T_a = 25^\circ\text{C}$

Parameter	Symbol	Min	Max	Unit
Forward Voltage at $I_F = 1\text{ A}$	$V_F$	-	0.45	V
Reverse Current at $V_R = 20\text{ V}$	$I_R$	-	200	$\mu\text{A}$

Note: ESD sensitive product handling required.

**TOP DYNAMIC**



Dated : 13/12/2012

● **Electrical characteristic curves (Ta=25°C)**

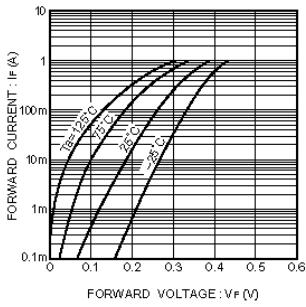


Fig.1 Forward characteristics

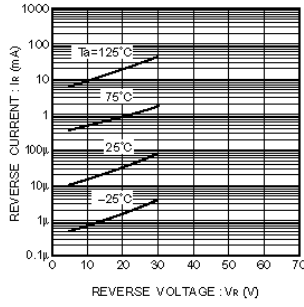


Fig.2 Reverse characteristics

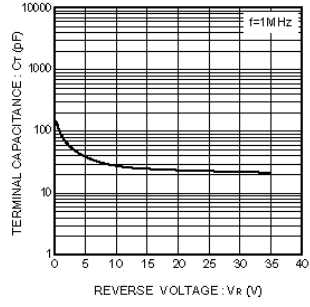


Fig.3 Capacitance between terminals characteristics

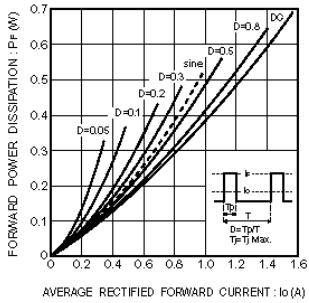


Fig.4 Forward power dissipation characteristics

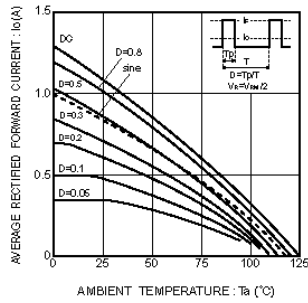


Fig.5 Derating curve (Io - Ta)